REMARKS

In further reply to the Office Action mailed November 26, 2001 and supplemental to the Amendment filed February 26, 2002, claims 1, 4-6, 10, 11, 15, 23, and 25-28 are amended to better define the scope of the claimed invention. Claims 1-27 were pending in the application, with claims 12-14, 22 and 24 being withdrawn from consideration. No claims have been canceled or added. Therefore, claims 1-30 are pending in the application, with claims 1-11, 15-21, 23 and 25-31 submitted for reconsideration.

Claims 1, 4-6, 10, 11, 15, 23, and 25-28 have been amended to delete the term "composed" and replace it with the term --including-- that better defines the applicants' invention. Furthermore, it should be noted that the instant amendments are not narrowing amendments within the meaning of the *Festo* case. No new matter has been added.

In view of the foregoing, applicants believe that the application is in condition for allowance. An early notice to this effect is earnestly solicited. If there are any questions regarding the application or if an examiner's amendment would facilitate the allowance of one or more of the claims, the examiner is invited to contact the undersigned attorney at the local telephone number below.

Respectfully submitted,

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Date

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Attached: Attachment A

Should additional fees be necessary in connection with the filing of this paper, or if a petition for extension of time is required for timely acceptance of same, the Commissioner is hereby authorized to charge deposit account No. 19-0741 for any such fees; and applicants hereby petition for any needed extension of time.

ATTACHMENT A

Marked up version of claim amendments made in the Amendment filed March 7, 2002

1. (Twice Amended) A semiconductor device comprising:

a pair of main electrodes used as source and drain electrodes;

an insulating gate film adjacent to the pair of main electrodes; and

a gate electrode comprising of a first region [composed] including at least a first group IV element and a second group IV element and formed in contact with the insulating gate film, and a second region [composed of] including the first group IV element and formed on the first region.

4. (Twice Amended) A semiconductor device comprising:

an insulated gate field effect transistor comprising a pair of main electrodes used as a source and drain electrodes, an insulating gate film adjacent to the pair of main electrodes, and a gate electrode comprising a first region [composed of] including at least a first group IV element and a second group IV element and formed in contact with the insulating gate film, and a second region [composed of] including the first group IV element and formed on the first region; and

a silicide electrode formed in contact with the second region of the gate electrode, and being substantially free from the second group IV element.

5. (Twice Amended) The semiconductor device of claim 4, wherein the first group IV element of the gate electrode is Si (silicon), the second group IV element of the gate electrode is Ge (germanium), and the silicide electrode [is composed of] includes a $CoSi_y$, or $TiSi_y$ layer which is substantially free from Ge.

6. (Twice Amended) The semiconductor device of claim 5, wherein the first region of the gate electrode has a thickness larger than a width of a depletion layer of the gate electrode [composed of] that includes Si.

10. (Twice Amended) The semiconductor device of claim 4, wherein the first group IV element of the gate electrode is Si, the second group IV element of the gate electrode is C (carbon), and the silicide electrode [is composed of] includes a $CoSi_y$, or $TiSi_y$ layer which is substantially free of C.

11. (Twice Amended) A semiconductor device comprising:

an insulated gate field effect transistor having a pair of main electrodes used as source and drain electrodes, an insulating gate film adjacent to the pair of main electrodes, and a gate electrode comprising a first region [composed of] including at least a first group IV element and a second group IV element and formed in contact with the insulating gate film, and a second region [composed of] including a multiple element compound including at least the first and second group IV elements and metal, and formed on the first region; and

a silicide electrode formed in contact with the second region of the gate electrode, [composed of] including the first group IV element and metal, and being substantially free from the second group IV element.

15. (Twice Amended) A semiconductor device comprising:

a semiconductor region of a first conductivity type;

an epitaxial growth layer formed on the semiconductor region and having a first region of the first conductivity type [composed of] including at least a first group IV element and a second group IV element and formed in contact with the semiconductor region and a second region of the first conductivity type [composed of] including the first group IV element and formed in contact with the first region; and

a silicide electrode formed on the second region of the epitaxial growth layer.

23. (Twice Amended) A semiconductor device comprising:

an insulated gate field effect transistor having a pair of main electrodes used as source and drain electrodes, an insulating gate film adjacent to the pair of main electrodes, and a gate electrode comprising a first region [composed of] including at least a first group IV element

and a second group IV element and formed in contact with the insulating gate film, and a second region [composed of] including the first group IV element and formed on the first region;

a respective elevated electrode formed on the main electrodes, and having a third region [composed of] including a third group IV element and a fourth group IV element and a fourth region formed on the third region and [composed of] including the third group IV element;

a first silicide electrode formed in contact with the second region of the gate electrode, and being substantially free from the second group IV element; and

a second silicide electrode formed in contact with the fourth region of the elevated electrode, and being substantially free from the fourth group IV element.

25. (Twice Amended) The semiconductor device of claim 1, wherein a layer is added between the insulating gate film and the first region of the gate electrode, is thinner than the first region, and [is composed of] includes the first group IV element or the second group IV element.

26. (Twice Amended) The semiconductor device of claim 4, wherein a layer is added between the insulating gate film and the first region of the gate electrode, is thinner than the first region, and [is composed of] includes the first group IV element or the second group IV element.

27. (Twice Amended) The semiconductor device of claim 11, wherein a layer is added between the insulating gate film and the first region of the gate electrode, is thinner than the first region, and [is composed of] includes the first group IV element or the second group IV element.

28. (Amended) A semiconductor device comprising:

an insulated gate field effect transistor having a pair of main electrodes used as source and drain electrodes of a first conductivity type, an insulating gate film adjacent to the a pair

of main electrodes, and a gate electrode comprising a first region [composed of] including at least a first group IV element and a second group IV element and formed in contact with the insulating gate film, and a second region [composed of] including the first Group IV element and formed in contact with the first region;

a respective elevated electrode of the first conductivity type formed on the main electrodes, and having a third region [composed of] including a third Group IV element and a fourth Group IV element and formed in contact with the respective main electrodes, and a fourth region formed in contact with the third region and [composed of] including the third Group IV element;

a first silicide electrode formed in contact with the second region of the gate electrode, and being substantially free from the second Group IV element; and

a second silicide electrode formed in contact with the fourth region of the elevated electrode, and being substantially free from the fourth Group IV element.